

In the Claims

Claims 1-72 (cancelled).

Claim 73 (new): A semiconductor processing patterning method, comprising:

forming a first and second resist layers over a surface of a silicon-comprising substrate, the first layer being both beneath the second layer and having a thickness which is less than a thickness of the second resist layer;

forming a mask pattern over the silicon-comprising substrate, the mask pattern comprising the first and second resist layers, wherein:

the first resist layer of the mask pattern comprises opposing sidewalls in at least one cross section, the first resist layer extending continuously between the opposing sidewalls of the first resist layer of the mask pattern;

the second resist layer of the mask pattern comprises opposing sidewalls in the one cross section, the second resist layer extending continuously between the opposing sidewalls of the second resist layer of the mask pattern; and

an entirety of the opposing sidewalls of the first resist layer received laterally inward of an entirety of the opposing sidewalls of the second resist layer in the one cross section; and

etching material of the silicon-comprising substrate using the mask pattern as a mask.

Claim 74 (new): The method of claim 73 wherein the first and second resist layers comprise different compositions as initially formed.

Claim 75 (new): The method of claim 73 wherein the first resist layer is photosensitive to electromagnetic radiation at a wavelength of no greater than about 325 nm.

Claim 76 (new): The method of claim 73 wherein both the first and second resist layers comprise negative resist.

Claim 77 (new): The method of claim 73 wherein both the first and second resist layers comprise positive resist.

Claim 78 (new): The method of claim 73 wherein the first resist layer comprises at least one of 1-methoxy-2-propanol and ethyl lactate and the second resist layer comprises at least one of cyclohexanone and 2-heptanone.

Claim 79 (new): The method of claim 73 wherein the first resist layer has a thickness which is less than a total thickness of all layers received over the first resist layer.

Claim 80 (new): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 50% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 81 (new): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 25% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 82 (new): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 10% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 83 (new): The method of claim 73 wherein the first resist layer has a thickness which is less than or equal to about 5% of a total thickness of the first resist layer and all layers received over the first resist layer.

Claim 84 (new): The method of claim 73 wherein the opposing sidewalls of the first resist layer are at least partially curved in the one cross section.

Claim 85 (new): The method of claim 73 wherein the opposing sidewalls of the first resist layer and the opposing sidewalls of the second resist layer are of different shapes in the one cross section.

Claim 86 (new): A semiconductor processing patterning method, comprising:

forming a first positive resist layer over a surface of a silicon-comprising substrate;

forming a second positive resist layer over the first positive resist layer, the first positive resist layer having a thickness less than the second positive resist layer;

forming a mask pattern over the silicon-comprising substrate, the mask pattern comprising the first and second positive resist layers, wherein:

the first positive resist layer comprises opposing sidewalls in at least one cross section, the first positive resist layer extending continuously between the opposing sidewalls of the first positive resist layer of the mask pattern;

the second positive resist layer comprises opposing sidewalls in at least the one cross section, the second positive resist layer extending continuously between the opposing sidewalls of the second positive resist layer of the mask pattern; and

at least a portion of the opposing sidewalls of the first positive resist layer of the mask pattern are recessed laterally inward of at least a portion of opposing sidewalls of the second positive resist layer in the one cross section; and

etching material of the silicon-comprising substrate using the mask pattern as a mask.

Claim 87 (new): The method of claim 86 wherein the first positive resist layer is photosensitive to electromagnetic radiation at a wavelength of no greater than about 325 nm.

Claim 88 (new): The method of claim 86 wherein the second positive resist layer is formed on the first positive resist layer.

Claim 89 (new): The method of claim 86 wherein the first positive resist layer comprises 1-methoxy-2-propanol and the second positive resist layer comprises cyclohexanone and 2-heptanone.

Claim 90 (new): The method of claim 86 wherein the first positive resist layer has a thickness which is less than a total thickness of all layers received over the first positive resist layer.

Claim 91 (new): The method of claim 86 wherein the first positive resist layer has a thickness which is from about 25% to about 50% of a total thickness of the first positive resist layer and all layers received over the first positive resist layer.

Claim 92 (new): The method of claim 86 wherein the first positive resist layer has a thickness which is from about 5% to about 10% of a total thickness of the first positive resist layer and all layers received over the first positive resist layer.

Claim 93 (new): The method of claim 86 wherein the first positive resist layer has a thickness which is less than about 5% of a total thickness of the first positive resist layer and all layers received over the first positive resist layer.

Claim 94 (new): The method of claim 86 wherein the opposing sidewalls of the first positive resist layer are at least partially curved in the one cross section.

Claim 95 (new): The method of claim 86 wherein an entirety of the opposing sidewalls of the first positive resist layer are recessed laterally inward of the opposing sidewalls of the second positive resist layer in the one cross section.